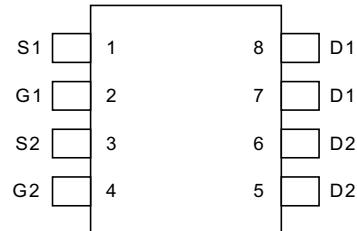


## Dual P-Channel Enhancement Mode MOSFET

## Features

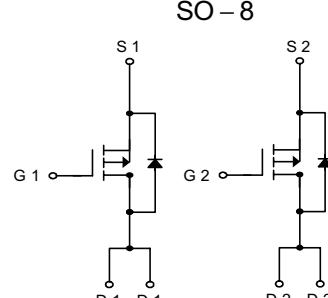
- 30V/-4.9A,  $R_{DS(ON)} = 53m\Omega$ (typ.) @  $V_{GS} = -10V$   
 $R_{DS(ON)} = 80m\Omega$ (typ.) @  $V_{GS} = -4.5V$
- Super High Density Cell Design
- Reliable and Rugged
- SO-8 Package

## Pin Description



## Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems



P-Channel MOSFET

## Ordering and Marking Information

|             |                  |               |  |
|-------------|------------------|---------------|--|
| APM4953     | □□-□□            | Handling Code | Package Code<br>K : SO-8                           |
|             |                  | Temp. Range   | Operation Junction Temp. Range<br>C : -55 to 150°C |
|             |                  | Package Code  | Handling Code<br>TU : Tube<br>TR : Tape & Reel     |
| APM4953 K : | APM4953<br>XXXXX |               | XXXXX - Date Code                                  |

## Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

| Symbol    | Parameter                          | Rating             | Unit |
|-----------|------------------------------------|--------------------|------|
| $V_{DSS}$ | Drain-Source Voltage               | -30                | V    |
| $V_{GSS}$ | Gate-Source Voltage                | $\pm 25$           |      |
| $I_D^*$   | Maximum Drain Current – Continuous | $T_A = 25^\circ C$ | A    |
| $I_{DM}$  | Maximum Drain Current – Pulsed     | -4.9               |      |
|           |                                    | -30                |      |

\* Surface Mounted on FR4 Board,  $t \leq 10$  sec.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

## Absolute Maximum Ratings (Cont.) ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Symbol            | Parameter                                | Rating                    | Unit                        |
|-------------------|--|---------------------------|-----------------------------|
| $P_D$             | Maximum Power Dissipation                | $T_A = 25^\circ\text{C}$  | 2.5                         |
|                   |  | $T_A = 100^\circ\text{C}$ | 1.0                         |
| $T_J$             | Maximum Junction Temperature             | 150                       | ${}^\circ\text{C}$          |
| $T_{STG}$         | Storage Temperature Range                | -55 to 150                |                             |
| $R_{\theta JA}^*$ | Thermal Resistance - Junction to Ambient | 50                        | ${}^\circ\text{C}/\text{W}$ |

## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

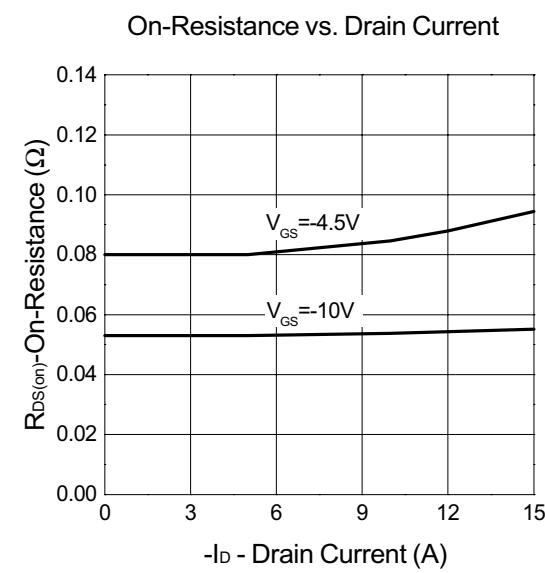
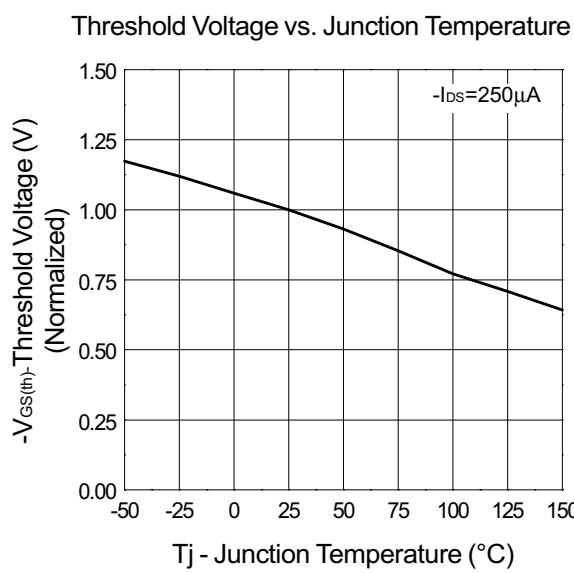
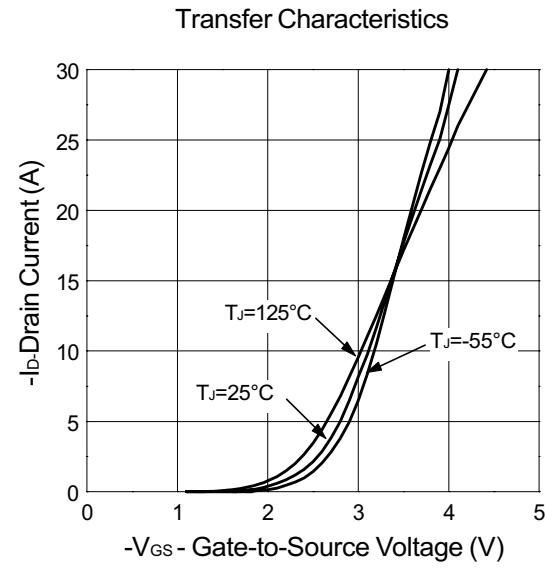
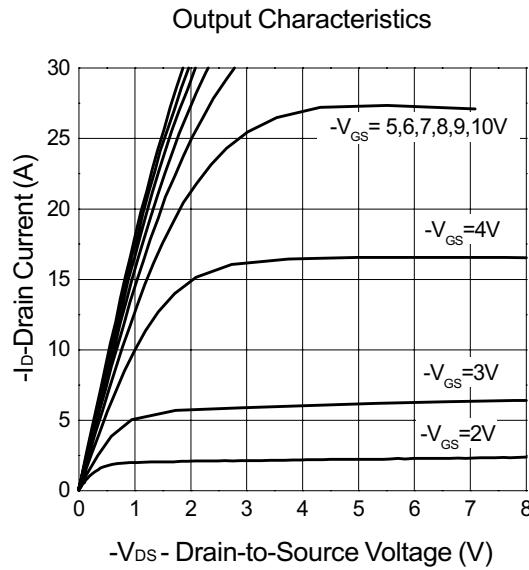
| Symbol                     | Parameter                                     | Test Condition  | APM4953 |                  |           | Unit             |
|----------------------------|---|---|---------|------------------|-----------|------------------|
|                            |   |   | Min.    | Typ <sup>a</sup> | Max.      |                  |
| <b>Static</b>              |   |   |         |                  |           |                  |
| $BV_{DSS}$                 | Drain-Source Breakdown Voltage                | $V_{GS}=0\text{V}$ , $I_{DS}=-250\mu\text{A}$   | -30     |                  |           | V                |
| $I_{DSS}$                  | Zero Gate Voltage Drain Current               | $V_{DS}=-24\text{V}$ , $V_{GS}=0\text{V}$   |         |                  | -1        | $\mu\text{A}$    |
| $V_{GS(\text{th})}$        | Gate Threshold Voltage                        | $V_{DS}=V_{GS}$ , $I_{DS}=-250\mu\text{A}$  | -1      | -1.5             | -2        | V                |
| $I_{GSS}$                  | Gate Leakage Current                          | $V_{GS}=\pm 25\text{V}$ , $V_{DS}=0\text{V}$  |         |                  | $\pm 100$ | nA               |
| $R_{DS(\text{ON})}$        | Drain-Source On-state Resistance <sup>b</sup> | $V_{GS}=-10\text{V}$ , $I_{DS}=-4.9\text{A}$  |         | 53               | 60        | $\text{m}\Omega$ |
|                            |   | $V_{GS}=-4.5\text{V}$ , $I_{DS}=-3.6\text{A}$   |         | 80               | 95        |                  |
| $V_{SD}$                   | Diode Forward Voltage <sup>b</sup>            | $I_{SD}=-1.7\text{A}$ , $V_{GS}=0\text{V}$  |         | -0.7             | -1.3      | V                |
| <b>Dynamic<sup>a</sup></b> |   |   |         |                  |           |                  |
| $Q_g$                      | Total Gate Charge                             | $V_{DS}=-15\text{V}$ , $I_{GS}=-10\text{V}$<br>$I_D=-4.6\text{A}$                                     |         | 22.3             | 29        | nC               |
| $Q_{gs}$                   | Gate-Source Charge                            |   |         | 4.65             |           |                  |
| $Q_{gd}$                   | Gate-Drain Charge                             |   |         | 2                |           |                  |
| $t_{d(\text{ON})}$         | Turn-on Delay Time                            | $V_{DD}=-15\text{V}$ , $I_D=-2\text{A}$ ,<br>$V_{GEN}=-10\text{V}$ , $R_G=6\Omega$<br>$R_L=7.5\Omega$ |         | 10               | 18        | ns               |
| $T_r$                      | Turn-on Rise Time                             |   |         | 15               | 20        |                  |
| $t_{d(\text{OFF})}$        | Turn-off Delay Time                           |   |         | 22               | 38        |                  |
| $T_f$                      | Turn-off Fall Time                            |   |         | 15               | 25        |                  |
| $C_{iss}$                  | Input Capacitance                             | $V_{GS}=0\text{V}$<br>$V_{DS}=-25\text{V}$<br>Frequency=1.0MHz  |         | 1260             |           | pF               |
| $C_{oss}$                  | Output Capacitance                            |   |         | 340              |           |                  |
| $C_{rss}$                  | Reverse Transfer Capacitance                  |   |         | 220              |           |                  |

### Notes

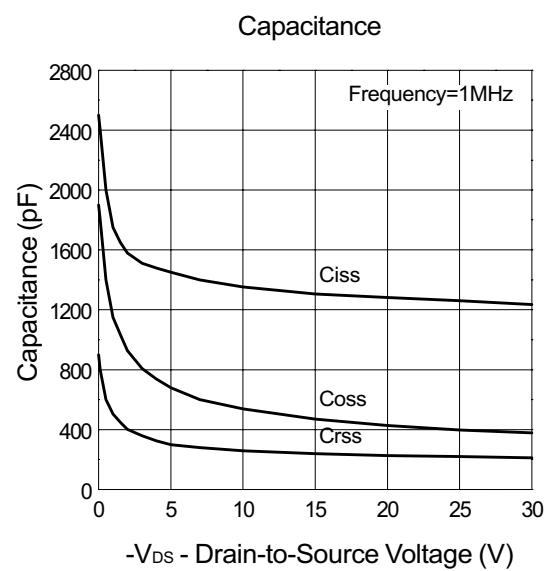
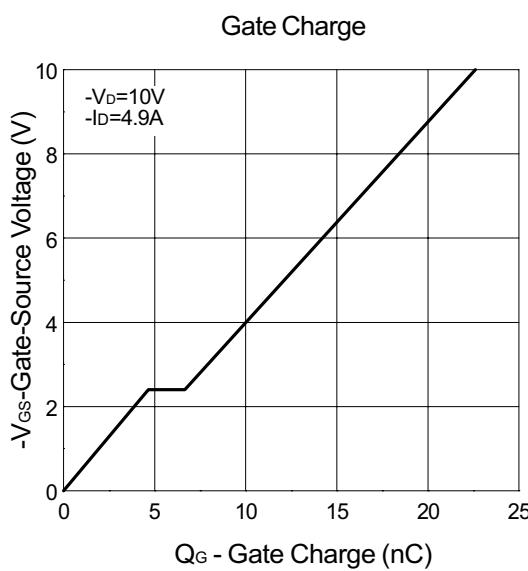
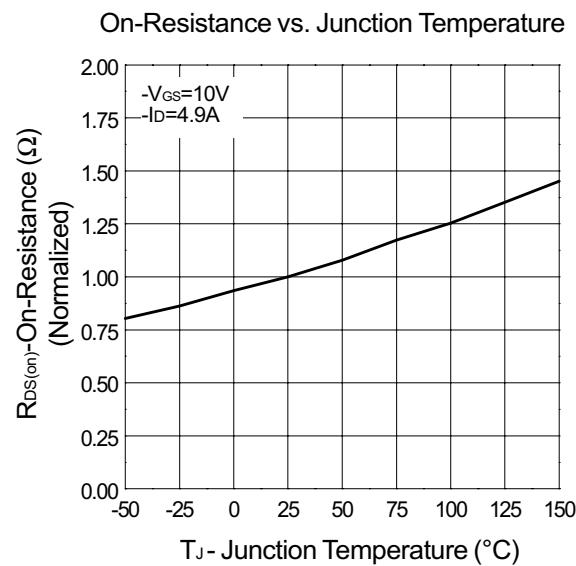
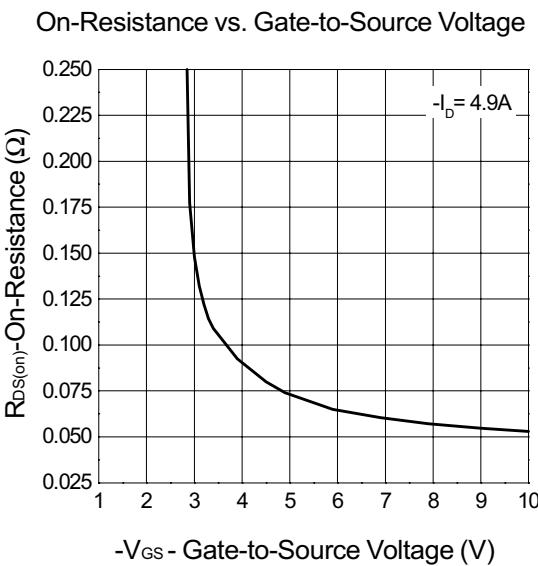
<sup>a</sup> : Pulse test ; pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$

<sup>b</sup> : Guaranteed by design, not subject to production testing

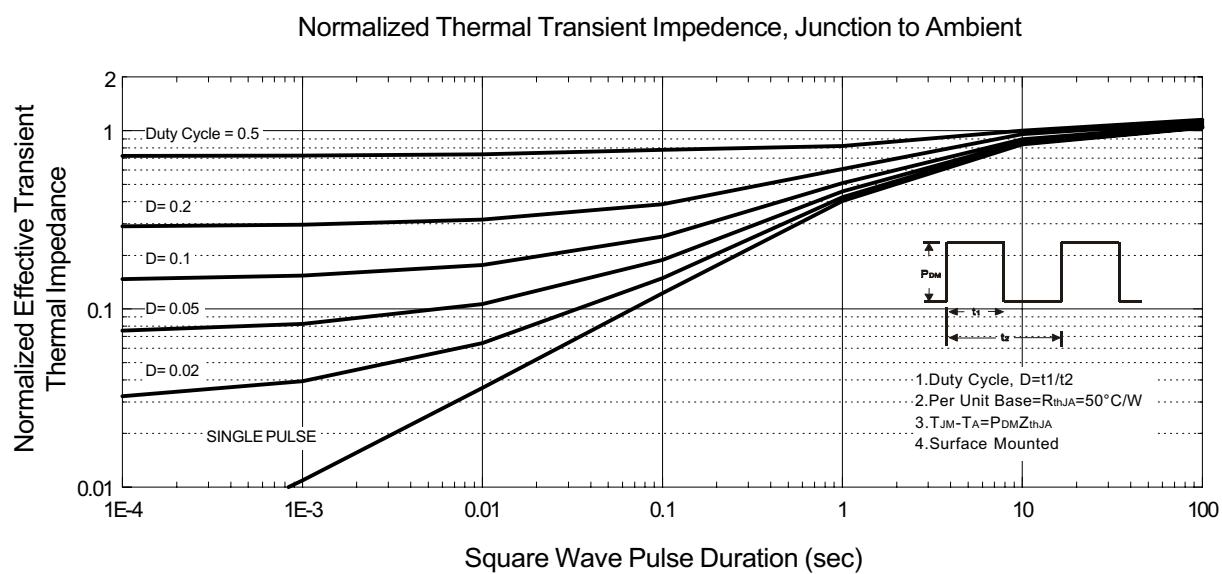
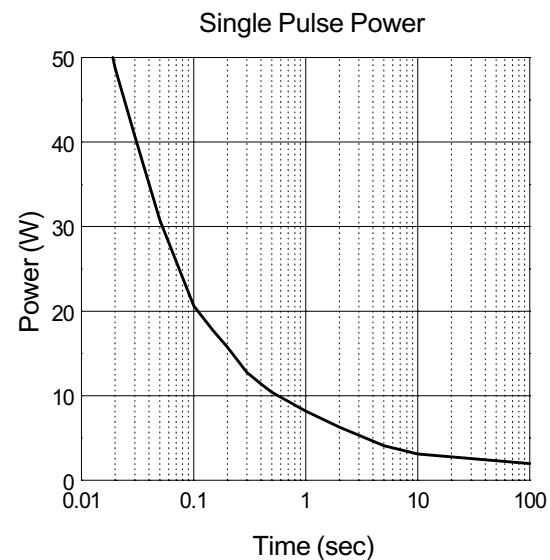
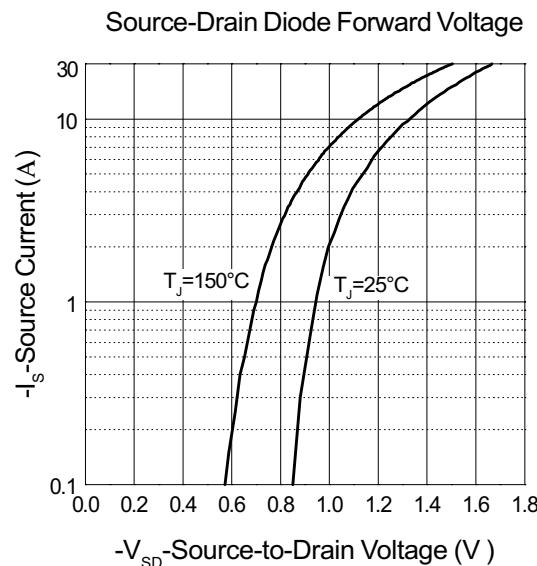
## Typical Characteristics



## Typical Characteristics (Cont.)

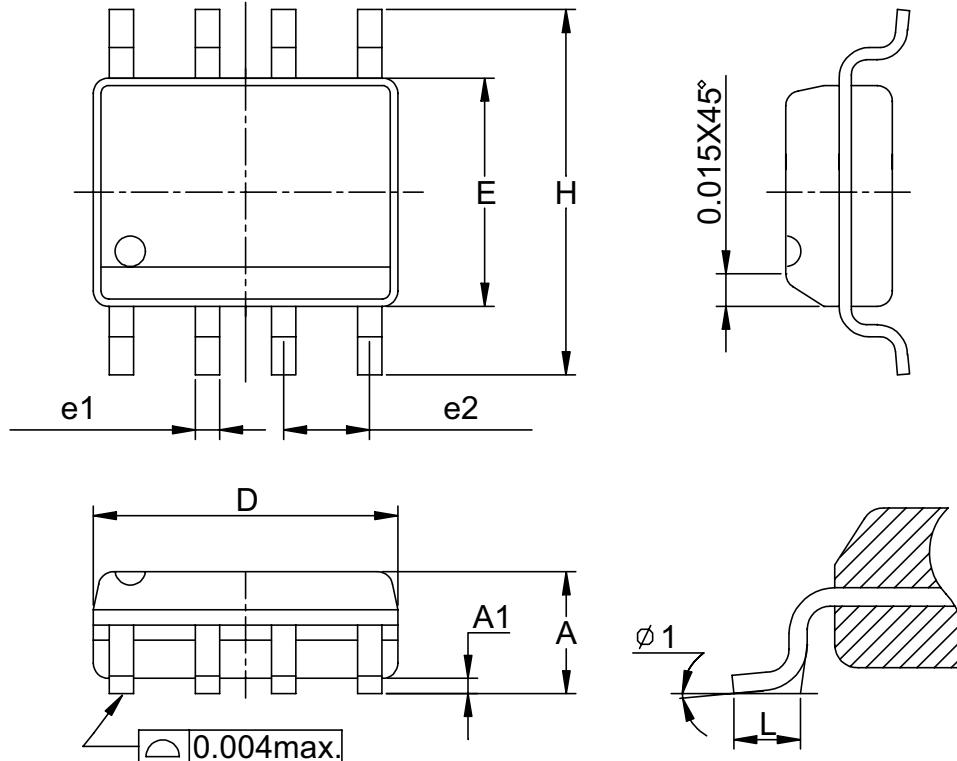


## Typical Characteristics (Cont.)



## Packaging Information

SOP-8 pin ( Reference JEDEC Registration MS-012)

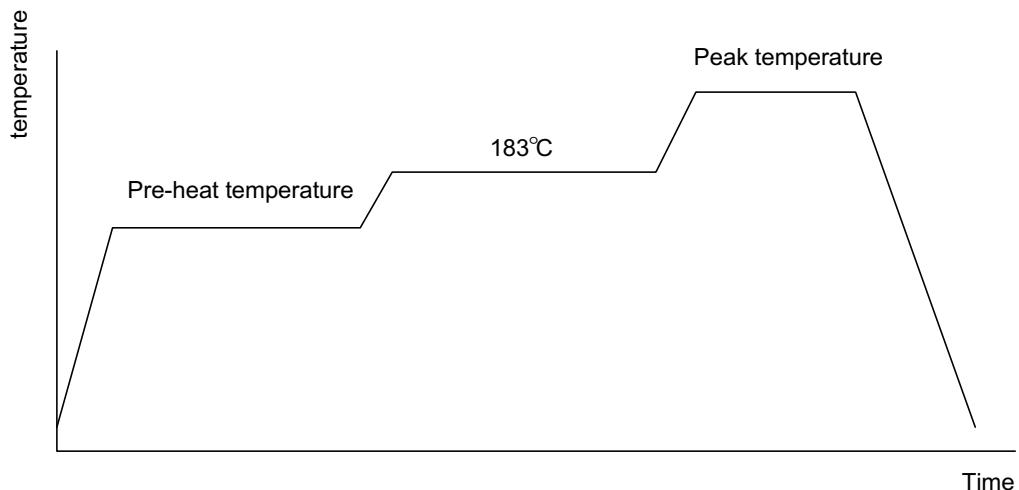


| Dim | Millimeters |      | Inches  |       |
|-----|-------------|------|---------|-------|
|     | Min.        | Max. | Min.    | Max.  |
| A   | 1.35        | 1.75 | 0.053   | 0.069 |
| A1  | 0.10        | 0.25 | 0.004   | 0.010 |
| D   | 4.80        | 5.00 | 0.189   | 0.197 |
| E   | 3.80        | 4.00 | 0.150   | 0.157 |
| H   | 5.80        | 6.20 | 0.228   | 0.244 |
| L   | 0.40        | 1.27 | 0.016   | 0.050 |
| e1  | 0.33        | 0.51 | 0.013   | 0.020 |
| e2  | 1.27BSC     |      | 0.50BSC |       |
| Ø 1 | 8°          |      | 8°      |       |

## Physical Specifications

|                    |  |
|--------------------|--|
| Terminal Material  | Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb) |
| Lead Solderability | Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3. |

### Reflow Condition (IR/Convection or VPR Reflow)



### Classification Reflow Profiles

|  | Convection or IR/<br>Convection | VPR                      |
|--|---------------------------------|--------------------------|
| Average ramp-up rate(183°C to Peak)        | 3°C/second max.                 | 10 °C /second max.       |
| Preheat temperature 125 ± 25°C             | 120 seconds max                 |                          |
| Temperature maintained above 183°C         | 60 – 150 seconds                |                          |
| Time within 5°C of actual peak temperature | 10 –20 seconds                  | 60 seconds               |
| Peak temperature range                     | 220 +5/-0°C or 235 +5/-0°C      | 215-219°C or 235 +5/-0°C |
| Ramp-down rate                             | 6 °C /second max.               | 10 °C /second max.       |
| Time 25°C to peak temperature              | 6 minutes max.                  |                          |

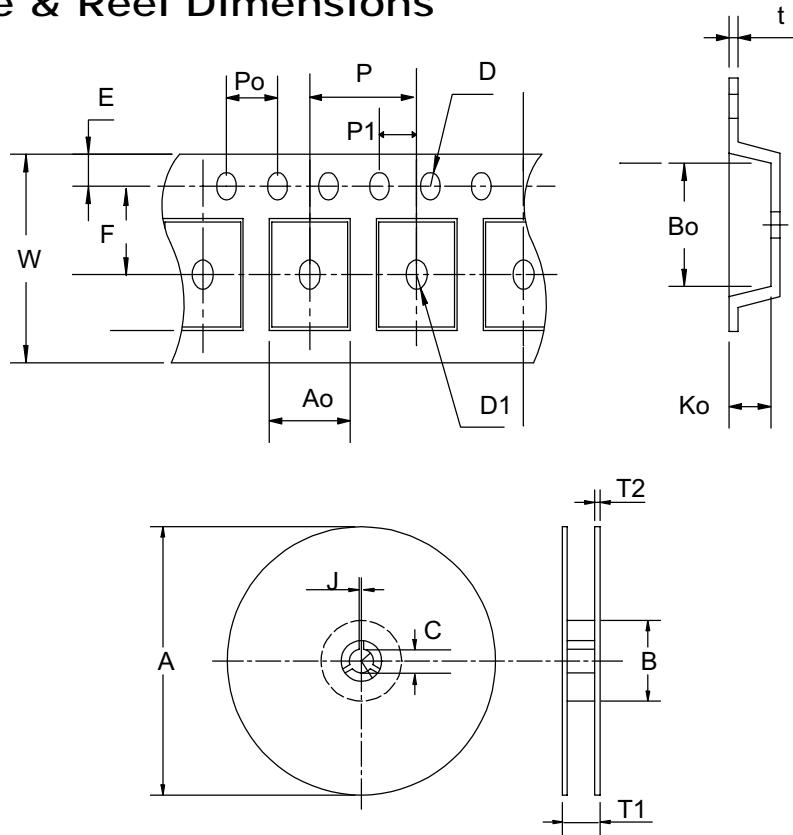
### Package Reflow Conditions

|  |   |   |
|--|---|---|
| <b>pkg. thickness ≥ 2.5mm<br/>and all bgas</b> | <b>pkg. thickness &lt; 2.5mm and<br/>pkg. volume ≥ 350 mm<sup>3</sup></b> | <b>pkg. thickness &lt; 2.5mm and pkg.<br/>volume &lt; 350mm<sup>3</sup></b> |
| Convection 220 +5/-0 °C                        |   | Convection 235 +5/-0 °C   |
| VPR 215-219 °C                                 |   | VPR 235 +5/-0 °C  |
| IR/Convection 220 +5/-0 °C                     |   | IR/Convection 235 +5/-0 °C  |

## Reliability test program

| Test item     | Method              | Description               |
|---------------|---------------------|---------------------------|
| SOLDERABILITY | MIL-STD-883D-2003   | 245°C, 5 SEC              |
| HOLT          | MIL-STD 883D-1005.7 | 1000 Hrs Bias @ 125°C     |
| PCT           | JESD-22-B, A102     | 168 Hrs, 100% RH, 121°C   |
| TST           | MIL-STD 883D-1011.9 | -65°C ~ 150°C, 200 Cycles |

## Carrier Tape & Reel Dimensions



| Application | A           | B           | C              | J             | T1             | T2            | W             | P             | E               |
|-------------|-------------|-------------|----------------|---------------|----------------|---------------|---------------|---------------|-----------------|
| SOP- 8      | $330 \pm 1$ | $62 +1.5$   | $12.75 + 0.15$ | $2 \pm 0.5$   | $12.4 \pm 0.2$ | $2 \pm 0.2$   | $12 \pm 0.3$  | $8 \pm 0.1$   | $1.75 \pm 0.1$  |
|             | F           | D           | D1             | Po            | P1             | Ao            | Bo            | Ko            | t               |
|             | $5.5 \pm 1$ | $1.55 +0.1$ | $1.55 + 0.25$  | $4.0 \pm 0.1$ | $2.0 \pm 0.1$  | $6.4 \pm 0.1$ | $5.2 \pm 0.1$ | $2.1 \pm 0.1$ | $0.3 \pm 0.013$ |

## Cover Tape Dimensions

| Application | Carrier Width | Cover Tape Width | Devices Per Reel |
|-------------|---------------|------------------|------------------|
| SOP- 8      | 12            | 9.3              | 2500             |

## Customer Service

### Anpec Electronics Corp.

#### Head Office :

5F, No. 2 Li-Hsin Road, SBIP,  
Hsin-Chu, Taiwan, R.O.C.

Tel : 886-3-5642000  
Fax : 886-3-5642050

#### Taipei Branch :

7F, No. 137, Lane 235, Pac Chiao Rd.,  
Hsin Tien City, Taipei Hsien, Taiwan, R. O. C.  
Tel : 886-2-89191368  
Fax : 886-2-89191369

# X-ON Electronics

Largest Supplier of Electrical and Electronic Components

***Click to view similar products for MOSFET category:***

***Click to view products by Anpec manufacturer:***

Other Similar products are found below :

[614233C](#) [648584F](#) [FDPF9N50NZ](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [FCA20N60\\_F109](#) [FDZ595PZ](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#)  
[405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T\)](#) [751625C](#) [PSMN4R2-30MLD](#)  
[TK31J60W5,S1VQ\(O\)](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#)  
[NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#)  
[IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [STU5N65M6](#) [C3M0021120D](#) [DMN13M9UCA6-7](#)  
[BSS340NWH6327XTSA1](#) [MCM3400A-TP](#) [DMTH10H4M6SPS-13](#) [IPS60R1K0PFD7SAKMA1](#) [IPS60R360PFD7SAKMA1](#)  
[IPS60R600PFD7SAKMA1](#) [IPS60R210PFD7SAKMA1](#) [DMN2990UFB-7B](#)